



PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/790,816	
			Filing Date	March 3, 2004	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2812	
			Examiner Name	Not Yet Assigned	
			Attorney Docket Number	M4065.0607/P607-A	
Sheet	1	of	4		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HD	**AA	2002/0031005	03/2002	Natori et al.	
	**AB	2002/0132417	09/09/2002	Li	
	**AC	2002/0160551	10/31/2002	Harshfield	
	**AD	2002/0168852	11/14/2002	Harshfield et al.	
	**AE	2002/0190289	12/19/2002	Harshfield et al.	
	**AF	2003/0032254	02/13/2003	Gilton	
	**AG	2003/0038301	02/27/2003	Moore	
	**AH	2003/0043631	03/06/2003	Gilton et al.	
	**AI	2003/0045049	03/06/2003	Campbell et al.	
	**AJ	2003/0045054	03/06/2003	Campbell et al.	
	**AK	2003/0047765	03/13/2003	Campbell	
	**AL	2003/0047772	03/13/2003	Li	
	**AM	2003/0047773	03/13/2003	Li	
	**AN	2003/0048519	03/13/2003	Kozicki	
	**AO	2003/0049912	03/13/2003	Campbell et al.	
	**AP	2003/0052330	03/2003	Klein	
	**AQ	2003/0068861	04/10/2003	Li	
	**AR	2003/0068862	04/10/2003	Li	
	**AS	2003/0095426	05/22/2003	Hush et al.	
	**AT	2003/0096497	05/22/2003	Moore et al.	
	**AU	2003/0107105	06/12/2003	Kozicki	
	**AV	2003/0117831	06/26/2003	Hush	
	**AW	2003/0128612	07/10/2003	Moore et al.	
	**AX	2003/0137869	07/24/2003	Kozicki	
	**AY	2003/0143782	07/31/2003	Gilton et al.	
	**AZ	2003/0155589	08/21/2003	Campbell et al.	
	**AA1	2003/0155606	08/21/2003	Campbell et al.	
	**AB1	2003/0156447	08/21/2003	Kozicki	
	**AC1	2003/0156463	08/21/2003	Casper et al.	
	**AD1	2003/0209728	11/13/2003	Kozicki et al	
	**AE1	2003/0209971	11/13/2003	Kozicki et al	
	**AF1	2003/0210564	11/13/2003	Kozicki et al	
	**AG1	2003/0212724	11/2003	Ovshinsky et al.	
	**AH1	2003/0048744	3/2003	Ovshinsky et al.	
	**A1	2003/0212725	11/2003	Ovshinsky et al.	
	**AJ1	2004/0035401	2/2004	Ramachandran et al.	
	**AK1	4,804,490	02/14/1989	Pryor et al.	
	**AL1	4,920,078	04/24/1990	Bagley et al.	
	**AM1	5,330,630	07/19/1994	Klersy et al.	
	**AN1	5,814,527	9/29/1998	Wolstenholme et al	
	**AO1	5,818,749	10/06/1998	Harshfield	
	**AP1	5,837,564	11/17/1998	Sandhu et al.	
	**AQ1	5,851,882	12/22/1998	Harshfield	
	**AR1	5,869,843	2/9/1999	Harshfield	

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Sheet	2	of	4	Attorney Docket Number	M4065.0607/P607-A

#1	**AS1	5,933,365	08/03/1999	Klersy et al.	
	**AT1	5,976,928	11/19999	Kirlin et al.	
	**AU1	6,031,287	2/29/2000	Harshfield	
	**AV1	6,420,725	7/16/2002	Harshfield	
	**AW1	6,440,837	8/27/2002	Harshfield	
	**AX1	6,518,636	02/2003	Segawa et al.	
	**AY1	RE 37,259E	7/2001	Ovshinsky	
	**AZ1	3,271,591	9/1966	Ovshinsky	
	**AA2	3,961,314	6/1976	Klose et al.	
	**AB2	3,966,317	6/1976	Wacks et al.	
	**AC2	3,983,542	11/1976	Ovshinsky	
	**AD2	3,988,720	10/1976	Ovshinsky	
	**AE2	4,177,474	12/1979	Ovshinsky	
	**AF2	4,267,261	5/1981	Hallman et al.	
	**AG2	4,597,162	7/1986	Johnson et al.	
	**AH2	4,608,296	8/1986	Keem et al.	
	**AI2	4,637,895	1/1987	Ovshinsky et al.	
	**AJ2	4,646,266	2/1987	Ovshinsky et al.	
	**AK2	4,664,939	5/1987	Ovshinsky	
	**AL2	4,668,968	5/1987	Ovshinsky et al.	
	**AM2	4,670,763	6/1987	Ovshinsky et al.	
	**AN2	4,673,957	6/1987	Ovshinsky et al.	
	**AO2	4,678,679	7/1987	Ovshinsky	
	**AP2	4,696,758	9/1987	Ovshinsky et al.	
	**AQ2	4,698,234	10/1987	Ovshinsky et al.	
	**AR2	4,710,899	12/1987	Young et al.	
	**AS2	4,728,406	3/1988	Banerjee et al.	
	**AT2	4,737,379	4/1988	Hudgens et al.	
	**AU2	4,766,471	8/1988	Ovshinsky et al.	
	**AV2	4,769,338	9/1988	Ovshinsky et al.	
	**AW2	4,775,425	10/1988	Guha et al.	
	**AX2	4,788,594	11/1988	Ovshinsky et al.	
	**AY2	4,809,044	2/1989	Pryor et al.	
	**AZ2	4,818,717	4/1989	Johnson et al.	
	**AA3	4,843,443	6/1989	Ovshinsky et al.	
	**AB3	4,845,533	7/1989	Pryor et al.	
	**AC3	4,853,785	8/1989	Ovshinsky et al.	
	**AD3	4,891,330	1/1990	Guha et al.	
	**AE3	5,128,099	7/1992	Strand et al.	
	**AF3	5,159,661	10/1992	Ovshinsky et al.	
	**AG3	5,166,758	11/1992	Ovshinsky et al.	
	**AH3	5,177,567	1/1993	Klersy et al.	
	**AI3	5,296,716	3/1994	Ovshinsky et al.	
	**AJ3	5,335,219	8/1994	Ovshinsky et al.	
	**AK3	5,359,205	10/1994	Ovshinsky	
	**AL3	5,341,328	8/1994	Ovshinsky et al.	
	**AM3	5,406,509	4/1995	Ovshinsky et al.	
	**AN3	5,414,271	5/1995	Ovshinsky et al.	
	**AO3	5,534,711	7/1996	Ovshinsky et al.	

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		First Named Inventor	Terry L. Gilton		
		Art Unit	2812		
		Examiner Name	Not Yet Assigned		
Sheet	3	of	4	Attorney Docket Number	M4065.0607/P607-A

(H)	**AP3	5,534,712	7/1996	Ovshinsky et al.	
	**AQ3	5,536,947	7/1996	Klersy et al.	
	**AR3	5,543,737	8/1996	Ovshinsky	
	**AS3	5,591,501	1/1997	Ovshinsky et al.	
	**AT3	5,596,522	1/1997	Ovshinsky et al.	
	**AU3	5,687,112	11/1997	Ovshinsky	
	**AV3	5,694,054	12/1997	Ovshinsky et al.	
	**AW3	5,714,768	2/1998	Ovshinsky et al.	
	**AX3	5,825,046	10/1998	Czubatyj et al.	
	**AY3	5,912,839	6/1999	Ovshinsky et al.	
	**AZ3	5,933,365	8/1999	Klersy et al.	
	**AA4	6,011,757	1/2000	Ovshinsky	
	**AB4	6,087,674	7/2000	Ovshinsky et al.	
	**AC4	6,141,241	10/2000	Ovshinsky et al.	
	**AD4	6,339,544	1/2002	Chiang et al.	
	**AE4	6,404,665	6/2002	Lowery et al.	
	**AF4	6,429,064	8/2002	Wicker	
	**AG4	6,437,383	8/2002	Xu	
	**AH4	6,462,984	10/2002	Xu et al.	
	**AI4	6,480,438	11/2002	Park	
	**AJ4	6,487,113	11/2002	Park et al.	
	**AK4	6,501,111	12/2002	Lowery	
	**AL4	6,507,061	1/2003	Hudgens et al.	
	**AM4	6,511,862	1/2003	Hudgens et al.	
	**AJN	6,511,867	1/2003	Lowery et al.	
	**AO4	6,512,241	1/2003	Lai	
	**AP4	6,514,805	2/2003	Xu et al.	
	**AQ4	6,531,373	3/2003	Gill et al.	
	**AR4	6,534,781	3/2003	Dennison	
	**AS4	6,545,287	4/2003	Chiang	
	**AT4	6,545,907	4/2003	Lowery et al.	
	**AU4	6,555,860	4/2003	Lowery et al.	
	**AV4	6,563,164	5/2003	Lowery et al.	
	**AW4	6,566,700	5/2003	Xu	
	**AX4	6,567,293	5/2003	Lowery et al.	
	**AY4	6,569,705	5/2003	Chiang et al.	
	**AZ4	6,570,784	5/2003	Lowery	
	**AA5	6,576,921	6/2003	Lowery	
	**AB5	6,586,761	7/2003	Lowery	
	**AC5	6,589,714	7/2003	Maimon et al.	
	**AD5	6,590,807	7/2003	Lowery	
	**AE5	6,593,176	7/2003	Dennison	
	**AF5	6,597,009	7/2003	Wicker	
	**AG5	6,605,527	8/2003	Dennison et al.	
	**AH5	6,613,604	9/2003	Maimon et al.	
	**AI5	6,621,095	9/2003	Chiang et al.	
	**AJ5	6,625,054	9/2003	Lowery et al.	
	**AK5	6,642,102	11/2003	Xu	
(H)	**AL5	6,646,297	11/2003	Dennison	

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				Art Unit	2812
				Examiner Name	Not Yet Assigned
Sheet	4	of	4	Attorney Docket Number	M4065.0607/P607-A

H1	**AM5	6,649,928	11/2003	Dennison	
	**AN5	6,667,900	12/2003	Lowery et al.	
	**AO5	6,671,710	12/2003	Ovshinsky et al.	
	**AP5	6,673,700	1/2004	Dennison et al.	
	**AQ5	6,674,115	1/2004	Hudgens et al.	
	**AR5	6,687,427	2/2004	Ramalingam et al.	
	**AS5	6,690,026	2/2004	Peterson	
	**AT5	6,696,355	2/2004	Dennison	
	**AU5	6,687,153	2/2004	Lowery	
	**AV5	6,707,712	3/2004	Lowery	
	**AW5	6,714,954	3/2004	Ovshinsky et al.	
H1	**AX5	6,673,648	01/2004	Lowrey	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					

Examiner Signature	<i>Heather Doty</i>	Date Considered	10/25/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/124,792 10/790 816	
			Filing Date	April 10, 2002 3/3/04	
			First Named Inventor	Terry L. Gilton	
			Art Unit	1773	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	10	Attorney Docket Number	M4065.0607/P607

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code² (if known)			
W	AA	6,388,324**	05/14/2002	Kozicki et al.	
	AB	US 2002/0000666**	01/03/2002	Kozicki et al.	
	AC	5,500,532**	03/19/1996	Kozicki et al.	
	AD	6,418,049**	07/09/2002	Kozicki et al.	
	AE	5,751,012**	05/12/1998	Wolstenholme et al.	
	AF	5,789,277**	08/04/1998	Zahorik et al.	
	AG	6,348,365**	02/19/2002	Moore et al.	
	AH	5,761,115**	06/02/1998	Kozicki et al.	
	AI	5,896,312**	04/20/1999	Kozicki et al.	
	AJ	5,914,893**	06/22/1999	Kozicki et al.	
	AK	6,084,796**	07/04/2000	Kozicki et al.	
HD	AL	US 2002/0168820**	11/14/2002	Kozicki et al.	
HD	AM	6,469,364**	10/22/2002	Kozicki	
HD	AN	2002/0072188 App**	6/2002	Gilton	
	AO	2002/0123169 App**	9/2002	Moore et al.	
	AP	2002/0123248 App. **	9/2002	Moore et al.	
	AQ	3,622,319**	11/1971	Sharp	
	AR	3,743,847**	7/1973	Boland	
	AS	4,269,935**	5/1981	Masters et al.	
	AT	4,312,938**	1/1982	Drexler, et al.	
	AU	4,316,946**	1/1982	Masters, et al.	
	AV	4,320,191**	3/1982	Yoshikawa et al.	
	AW	4,405,710**	9/1983	Balasubramanyam et al.	
	AX	4,419,421**	12/1983	Wichelhaus, et al.	
	AY	4,795,657**	1/1989	Formigoni et al.	
	AZ	4,847,674**	7/1989	Sliwa et al.	
	AA1	4,499,557**	2/1985	Holmberg et al.	
	AB1	5,177,567**	1/1993	Klersy et al.	
	AC1	5,219,788**	6/1993	Abernathay et al.	
	AD1	5,238,862**	8/1993	Blalock et al.	
	AE1	5,315,131**	5/1994	Kishimoto et al.	
	AF1	5,350,484**	9/1994	Gardner et al.	
	AG1	5,360,981**	11/1994	Owen et al.	
	AH1	5,512,328**	4/1996	Yoshimura et al.	
	AI1	5,512,773**	4/1996	Wolf et al.	
	AK1	5,726,083**	3/1998	Takaishi	
	AL1	5,841,150**	11/1998	Gonzalez et al.	
	AM1	5,846,889**	12/1998	Harbison et al.	
	AN1	5,920,788**	7/1999	Reinberg	
	AO1	5,998,066**	12/1999	Block et al.	
	AP1	6,077,729**	6/2000	Harshfield	
	AQ1	6,117,720**	9/2000	Harshfield	
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	40/121,702
				Filing Date	April 10, 2002
				First Named Inventor	Terry L. Gilton
				Art Unit	1773
				Examiner Name	Not Yet Assigned
Sheet	2	of	10	Attorney Docket Number	M4065.0607/P607

41)	AT1	6,236,059**	5/2001	Wolstenholme et al.	
	AU1	6,297,170**	10/2001	Gabriel et al.	
	AV1	6,300,684**	10/2001	Gonzalez et al.	
	AW1	6,316,784**	11/2001	Zahorik et al.	
	AX1	6,329,606**	12/2001	Freyman et al.	
	AY1	6,350,679**	2/2002	McDaniel et al.	
	AZ1	6,376,284**	4/2002	Gonzalez et al.	
	AA2	6,391,688**	5/2002	Gonzalez et al.	
	AB2	6,414,376**	7/2002	Thakur et al.	
	AC2	6,423,628**	7/2002	Li et al.	
	AD2	6,487,106**	11/26/2002	Kozicki	
	AE2	5,314,772**	5/24/1994	Kozicki	
	AF2	2002/0190350 APP**	12/19/2002	Kozicki	
	AG2	2003/0027416 APP**	2/6/2003	Moore	
	AH2	2003/0001229 APP**	1/2/2003	Moore et al.	
	AI2	2002/0106849 APP**	8/8/2002	Moore	
	AJ2	2002/0127886 APP**	9/12/2002	Moore et al.	
	AK2	2002/0123170 APP**	9/5/2002	Moore et al.	
	AL2	2002/0163828 APP**	11/2002	Krieger et al.	
	AM2	6,072,716**	6/2000	Jacobson et al.	
	AN2	5,272,359**	12/93	Nagasubramanian et al.	
	AO2	4,671,618**	6/87	Wu et al.	
	AP2	4,800,526**	1/89	Lewis	
	AQ2	2003/00353**14	02/20/03	Kozicki	
	AR2	2003/003531**5	02/20/03	Kozicki	
th)	AS2	6,473,332**	04/04/01	Ignatiev et al.	

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		Country Code ²	Number ³ -Kind Code ⁴ (if known)				
41)	BA	WO	02/21542**	03/14/2002	Kozicki et al.		
41)	BB	WO	00/48196**	08/17/2000	Kozicki et al.		
41)	BC	WO	97/48032**	12/18/1997	Kozicki et al.		
41)	BD	WO	99/28914**	06/10/1999	Kozicki et al.		
41)	BE	JP	56126916**	10/1981	Akira et al.		

Examiner Signature	<i>Heather Doty</i>	Date Considered	10/25/05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
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			Filing Date	April 10, 2002	
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			Group Art Unit	1773	
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
HA	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.**		
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HA	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.**		
HA	CD	Affifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.**		
HA	CE	Affifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.**		
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HA	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.**		
HA	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.**		
HA	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.**		
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Sheet	4	of	10	Attorney Docket Number	M4065.0607/P607

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			Application Number	10/121,791	
			Filing Date	April 10, 2002	
			First Named Inventor	Terry L. Gilton	
			Group Art Unit	1773	
			Examiner Name	Not Yet Assigned	
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		Application Number	10/124,791 10/790,816		
		Filing Date	April 10, 2002 3-3-04		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	1773		
		Examiner Name	Not Yet Assigned		
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Examiner Signature	<i>Heather Doty</i>	Date Considered	10/25/06
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